

PRELIMINARY AMENDMENT

Please add claims 6-14 to this application:

6. (New) A semiconductor device comprising:

a substrate, and

a multilayer formed on the substrate, the multilayer

comprising a semiconductor element and a dummy semiconductor element,

wherein the semiconductor element includes a first dielectric layer and an electrode on the first dielectric layer, and the first dielectric layer is composed of the material selected from a dielectric material having a dielectric constant of 100 or more and a ferroelectric material, and

wherein the dummy semiconductor element includes a second dielectric layer and a dummy electrode on the second dielectric layer,

and

wherein the dummy semiconductor element is located so that a space between the electrode and the dummy electrode is in a predetermined range, and

wherein the multilayer is produced by a method comprising:

forming a dielectric film for the first dielectric layer and the second dielectric layer;

forming an electrically conductive film on the dielectric film;

and

etching the electrically conductive film so as to form the electrode and the dummy electrode.

7. (New) A semiconductor device according to claim 6, wherein the predetermined range of the space is between 0.3 μ m and 14 μ m.

8. (New) A semiconductor device according to claim 6, wherein the method further comprises etching the dielectric film so as to form the first dielectric layer and the second dielectric layer.

9. (New) A semiconductor device according to claim 6, wherein the electrode is surrounded by the dummy electrode.

10. (New) A semiconductor device according to claim 6, wherein the semiconductor device is a transistor in which the electrode works as a gate of the transistor.

11. (New) A semiconductor device according to claim 6, wherein the semiconductor device is a capacitor element further comprising a bottom electrode between the first dielectric layer and the substrate, and the dummy semiconductor element is a dummy capacitor element further comprising a dummy bottom electrode between the second dielectric layer and the substrate, and

wherein the method further comprises forming a bottom electrically conductive film for the bottom electrode and the dummy bottom electrode between the dielectric film and the substrate.

12. (New) A semiconductor device according to claim 7, wherein the space is 9 μm or less.

13. (New) A semiconductor device according to claim 7, wherein the space is 5 μm or less.

14. (New) A semiconductor device according to claim 11, wherein the method further comprises etching the bottom electrically conductive film so as to form the bottom electrode and the dummy bottom electrode.